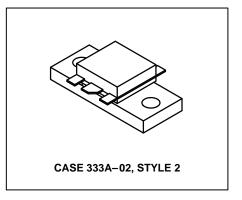
# The RF Line NPN Silicon RF Power Transistor

The MRF6414 is designed for 26 volt UHF large signal, common emitter, class AB linear amplifier applications.

- Specified 26 Volt, 960 MHz Characteristics
   Output Power = 50 Watts
   Minimum Gain = 8.5 dB @ 960 MHz, Class AB
   Minimum Efficiency = 50% @ 960 MHz, 50 Watts
- Silicon Nitride Passivated
- Gold Metallized, Emitter Ballasted for Long Life and Resistance to Metal Migration
- Circuit Board Photomaster Available by Ordering Document MRF6414PHT/D from Motorola Literature Distribution.

## **MRF6414**

50 W, 960 MHz RF POWER TRANSISTOR NPN SILICON



#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	28	Vdc
Collector–Base Voltage	V <sub>CBO</sub>	65	Vdc
Emitter–Base Voltage	VEBO	4	Vdc
Collector-Current — Continuous	IC	6	Adc
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	134 0.77	Watts W/°C
Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case		1.3	°C/W

#### **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

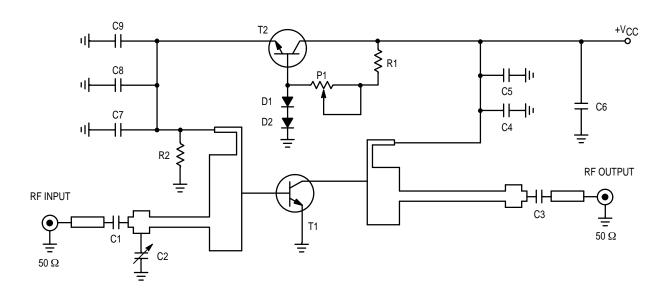
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = 20 mAdc, I <sub>B</sub> = 0)	V(BR)CEO	28	_	_	Vdc
Collector–Base Breakdown Voltage (I <sub>C</sub> = 20 mAdc, I <sub>E</sub> = 0)	V(BR)CBO	65	_	_	Vdc
Emitter-Base Breakdown Voltage (I <sub>E</sub> = 10 mAdc, I <sub>C</sub> = 0)	V(BR)EBO	4	_	_	Vdc
Collector–Emitter Leakage Current (V <sub>CE</sub> = 30 Vdc, R <sub>BE</sub> = 75 Ω)	ICER	_	_	10	mAdc
ON CHARACTERISTICS					
DC Current Gain (I <sub>CE</sub> = 1 Adc, V <sub>CE</sub> = 5 Vdc)	hFE	30		120	_



#### **ELECTRICAL CHARACTERISTICS** — **continued** ( $T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
DYNAMIC CHARACTERISTICS					
Output Capacitance $(V_{CB} = 26 \text{ Vdc}, I_E = 0, f = 1 \text{ MHz}) (1)$	C <sub>ob</sub>	_	45	_	pF
FUNCTIONAL TESTS					
Common–Emitter Amplifier Power Gain (V <sub>CC</sub> = 26 Vdc, P <sub>Out</sub> = 50 W, I <sub>CQ</sub> = 200 mA, f = 960 MHz)	G <sub>pe</sub>	8.5	_	_	dB
Collector Efficiency (V <sub>CC</sub> = 26 Vdc, P <sub>out</sub> = 50 W, I <sub>CQ</sub> = 200 mA, f = 960 MHz)	η	50	55	_	%
Output Mismatch Stress (V <sub>CC</sub> = 26 Vdc, P <sub>out</sub> = 50 W, I <sub>CQ</sub> = 200 mA, f = 960 MHz) VSWR = 3:1; all phase angles at frequency of test	Ψ	No Degradation in Output Power			

<sup>(1)</sup> For information only. It is not measurable in MRF6414 because of internal matching network.



C1, C3	100 pF, Chip Capacitor, Hight Q	P1	1 kΩ, Trimmer
C2, C7	330 pF, Chip Capacitor, 0805	R1	1 kΩ, Resistor
C5, C8	10 nF, Chip Capacitor, 0805	R2	58 $\Omega$ , Resistor, 0805
C6	15 μF, Capacitor, 63 V	T1	MRF6414
C9	100 μF, Capacitor, 16 V	T2	Transistor NPN Type BD135
D1, D2	Diode 1N4007		

Figure 1. 960 MHz Test Circuit Schematic

#### **TYPICAL CHARACTERISTICS**

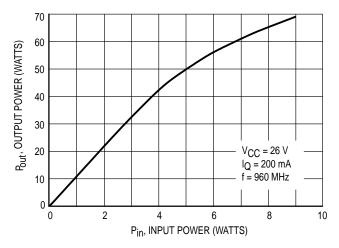


Figure 2. Output Power versus Input Power (Typical)

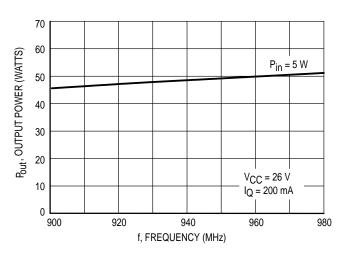


Figure 3. Output Power versus Frequency

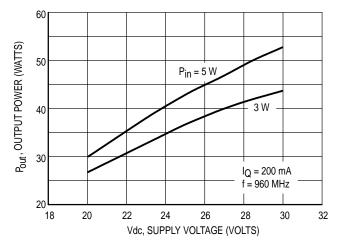


Figure 4. Output Power versus Supply Voltage

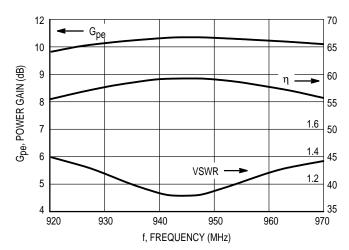


Figure 5. Typical Broadband Amplifier

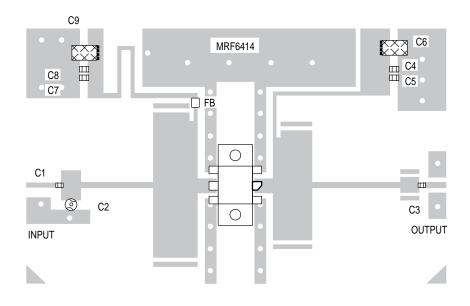
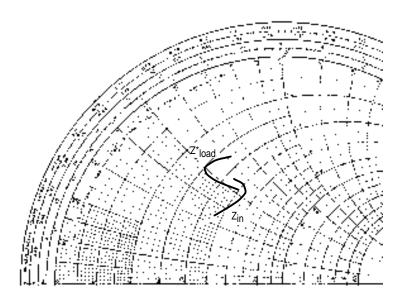


Figure 6. 960 MHz Test Circuit Components Layout



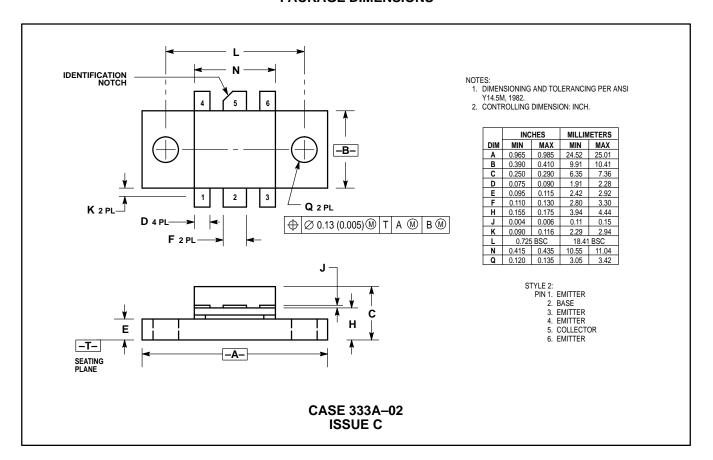
### Normalized to 10 $\Omega$

f MHz	Z <sub>in</sub> Ohms	Z <sub>OL</sub> * Ohms
900	4.4 + j4.6	4.7 + j4.7
935	5.1 + j4.8	4.0 + j3.9
960	5.4 + j3.6	3.7 + j4.5
980	4.7 + j2.5	3.4 + j4.7

Z<sub>OL</sub>\*: Conjugate of optimum load impedance into which the device operates at a given output power, voltage, current and frequency.

Figure 7. Input and Output Impedances with Circuit Tuned for Maximum Gain @  $V_{CC}$  = 26 V,  $I_Q$  = 200 mA,  $P_{out}$  = 50 W

#### **PACKAGE DIMENSIONS**



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